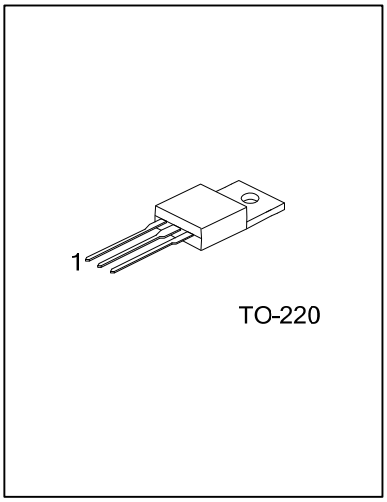
N-CHANNEL ENHANCEMENT MODE POWER MOSFET



■ DESCRIPTION

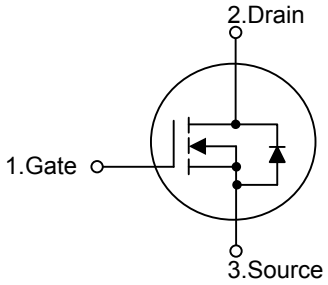
The UTC **UTT100N08** is an N-channel enhancement mode Power FET using UTC's advanced technology to provide customers with a minimum on-state resistance and superior switching performance.

It also can withstand high energy pulse in the avalanche and commutation mode.

■ FEATURES

* Fast switching speed
* $R_{DS(ON)}$= 7mΩ @ V_{GS}=10V
* Work below 175°C
* 100% avalanche tested
* Improved dv/dt capability

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTT100N08L-TA3-T	UTT100N08G-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

UTT100N08L-TA3-T

(1)Packing Type
(2)Package Type
(3)Lead Free

(1) T: Tube
(2) TA3: TO-220
(3) G: Halogen Free, L: Lead Free

■ ABSOLUTE MAXIMUM RATINGS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	80	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I_D	100	A
	Pulsed	I_{DM}	400	A
Avalanche Energy	Single Pulsed	E_{AS}	875	mJ
Peak Diode Recovery dv/dt		dv/dt	6	V/ns
Power Dissipation		P_D	83	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	°C/W
Junction to Case	θ_{JC}	1.5	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	80			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=60V, V_{GS}=0V			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	1		3	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=50A		7	12	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		1500		pF
Output Capacitance		C_{OSS}			1060		pF
Reverse Transfer Capacitance		C_{RSS}			700		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{GS}=10V, V_{DS}=30V, I_D=100A		500		nC
Gate to Source Charge		Q_{GS}			50		nC
Gate to Drain Charge		Q_{GD}			33		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=30V, VGS=10V, I_D≒100A, R_G=0.4Ω		90		ns
Rise Time		t_R			130	200	ns
Turn-OFF Delay Time		$t_{D(OFF)}$			768		ns
Fall-Time		t_F			280	420	ns
Transconductance		g_{FS}	V_{DS}=15V, I_D=30A	30			S
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S		100			A
Maximum Body-Diode Pulsed Current		I_{SM}		400			A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=100A, V_{GS}=0V		1.0	1.5	V
Resistance of Gate		R_G		0.65	1.3	2	Ω